BLP0427M9S20; BLP0427M9S20G Power LDMOS transistor Rev. 1 — 16 January 2018

AMPLEON

Product data sheet

Product profile

1.1 General description

20 W plastic LDMOS power transistor for general purpose applications at frequencies from 400 MHz to 2700 MHz.

Application performance (multiple frequencies)

Typical RF performance at T_{case} = 25 °C; I_{Da} = 180 mA; in a class-AB demo board, tested on gull wing lead device.

Test signal	f	I _{Dq}	V _{DS}	P _{L(AV)}	P _{L(1dB)}	Gp	η _D
	(MHz)	(mA)	(V)	(dBm)	(dBm)	(dB)	(%)
pulsed	960 to 1215	100	28	-	43	17	>55
1-carrier	1805 to 1880	180	28	35	-	19	21
CW	30 to 512	150	28	-	43	19	>50

Application performance

Typical RF performance at T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq} = 100 mA; t_p = 300 μ s; δ = 10 %; in a class-AB demo board, tested on straight lead device.

Test signal	f	P_L	G _p	P _{L(1dB)}	ησ	RLin
	(MHz)	(dBm)	(dB)	(dBm)	(%)	(dB)
pulsed RF	1200 to 1400	43	19	43	63	-9

1.2 Features and benefits

- High efficiency
- Excellent ruggedness
- Designed for broadband operation
- Excellent thermal stability
- High power gain
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Radars & avionics
- Broadcast transmitter applications
- Communications
- Industrial, scientific and medical applications

2. Pinning information

Table 3. Pinning

Pin	Description		Simplified outline	Graphic symbol
BLP0427	'M9S20 (SOT1482-1)			
1	drain		2	
2	gate			1
3	source	[1]	3 0	2 - 3 3 sym112
BLP0427	'M9S20G (SOT1483-1)			
1	drain		2	
2	gate			1
3	source	[1]	1	2 3 3 sym112

^[1] Connected to flange.

3. Ordering information

Table 4. Ordering information

Type number	Packag	Package				
	Name	Description	Version			
BLP0427M9S20	-	plastic; heatsink small outline package; 2 leads (flat)	SOT1482-1			
BLP0427M9S20G	-	plastic; heatsink small outline package; 2 leads	SOT1483-1			

4. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	225	°C

5. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _{case} = 80 °C; P _L = 3 W	1.1	K/W

6. Characteristics

Table 7. DC characteristics

 T_i = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.3 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 30 \text{ mA}$	1.5	2.0	-	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 180 mA	1.6	2.1	2.6	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V$	-	6	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	140	nA
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_{D} = 30 \text{ mA}$	-	300	-	mS
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 1.05 \text{ A}$	-	500	-	mΩ

Table 8. RF characteristics

A derivative functional RF test is performed in production. The performance as mentioned below is verified by design and characterization in a class AB production board.

Test signal: pulsed CW; δ = 10%; t_p = 100 μ s; V_{DS} = 28 V; I_{Dq} = 180 mA; T_{case} = 25 °C; f = 1842.5 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	$P_{L(AV)} = 35 \text{ dBm}$	17	19	-	dB
η_{D}	drain efficiency	$P_{L(AV)} = 35 \text{ dBm}$	18	22	-	%
RLin	input return loss	$P_{L(AV)} = 35 \text{ dBm}$	-	-10	-6	dB
P _{L(1dB)}	output power at 1 dB gain compression		-	42.5	-	dBm
P _{L(3dB)}	output power at 3 dB gain compression		-	43	-	dBm

7. Test information

7.1 Ruggedness in Doherty operation

The BLP0427M9S20 and BLP0427M9S20G are capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 28 \text{ V}$; $P_L = 20 \text{ W}$ (CW); f = 728 MHz and 1805 MHz on development board.

7.2 Impedance information

Table 9. Typical impedance of BLP0427M9S20G Measured load-pull data; $I_{Dq} = 180 \text{ mA}$; $V_{DS} = 28 \text{ V}$.

f	Z _S [1]	Z _L [1]	P _L [2]	η <mark>ρ ^[2]</mark>	G _p [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
Maximum pov	ver load				
740	0.5 + j0.1	10.6 – j1.0	37	55.1	22.8
880	0.6 – j1.4	3.8 + j2.0	49	70.9	22.8
1810	1.6 – j5.5	3.4 – j1.0	43	62.2	19.0
1840	1.3 – j5.8	3.0 – j1.2	43	62.7	19.1

BLP0427M9S20_0427M9S20G

Table 9. Typical impedance of BLP0427M9S20G ...continued

Measured load-pull data; $I_{Dq} = 180 \text{ mA}$; $V_{DS} = 28 \text{ V}$.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)
1880	1.3 – j6.2	2.6 – j1.5	42	61.2	18.7
2110	5.3 – j9.6	2.6 – j2.5	41	58.2	17.7
2170	6.2 – j8.1	2.6 – j2.5	41	60.4	18.2
Maximum dra	in efficiency load				
740	0.5 + j0.1	6.0 + j10.0	20	74.1	24.8
880	0.6 – j1.4	3.7 + j5.9	26	82.7	24.7
1810	1.6 – j5.5	1.9 + j0.2	31	70.9	20.9
1840	1.3 – j5.8	1.7 + j0.0	29	69.8	21.3
1880	1.3 – j6.2	1.6 – j0.2	28	69.8	21.3
2110	5.3 – j9.6	1.7 – j1.5	32	65.6	19.5
2170	6.2 – j8.1	1.6 – j1.7	30	65.9	20.2

^[1] Z_S and Z_L defined in Figure 1.

Table 10. Typical impedance of BLP0427M9S20

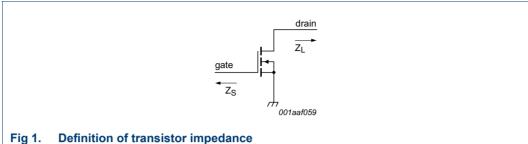
Measured load-pull data; $I_{Dq} = 180 \text{ mA}$; $V_{DS} = 28 \text{ V}$.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum pov	Maximum power load									
740	0.6 + j0.6	10.6 – j1.0	39	56.8	22.7					
880	0.6 - j0.7	4.0 + j1.6	51	70.9	22.1					
1810	1.8 – j5.4	3.0 – j1.2	44	60.9	19.1					
1840	1.6 – j5.8	3.0 – j1.2	44	62.6	19.6					
1880	1.8 – j6.1	2.9 – j1.6	44	60.9	19.1					
2110	7.3 – j8.2	2.6 – j2.5	41	57.7	17.8					
2170	8.7 – j6.8	2.6 – j2.5	43	62.1	18.7					
Maximum dra	in efficiency load									
740	0.6 + j0.6	6.0 + j10.0	22	77.0	24.6					
880	0.6 - j0.7	3.7 + j5.9	26	85.3	24.4					
1810	1.8 – j5.4	1.9 + j0.0	33	69.4	20.9					
1840	1.6 – j5.8	1.9 + j0.0	31	69.4	21.7					
1880	1.8 – j6.1	1.8 – j0.2	32	70.7	21.6					
2110	7.3 – j8.2	1.5 – j1.4	30	65.3	19.9					
2170	8.7 – j6.8	1.4 – j1.6	29	69.3	21.3					

^[1] Z_S and Z_L defined in <u>Figure 1</u>.

^[2] at 3 dB gain compression.

^[2] at 3 dB gain compression.



7.3 Test circuit

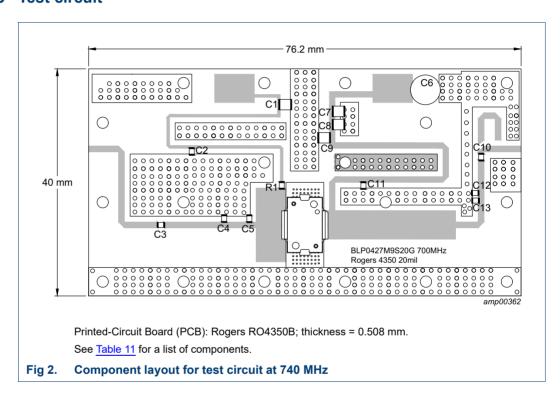


Table 11. List of components See Figure 2 for component layout.

Component	Description	Value	Remarks
C1, C7, C8, C9	multilayer ceramic chip capacitor	10 μF, 50 V	Murata
C2, C3, C10, C11	multilayer ceramic chip capacitor	36 pF	ATC 600F
C4, C5	multilayer ceramic chip capacitor	15 pF	ATC 600F
C6	electrolytic capacitor	2200 μF, 50 V	
C12	multilayer ceramic chip capacitor	5.6 pF	ATC 600F
C13	multilayer ceramic chip capacitor	0.2 pF	ATC 600F
R1	resistor	5.1 Ω	SMD 0805

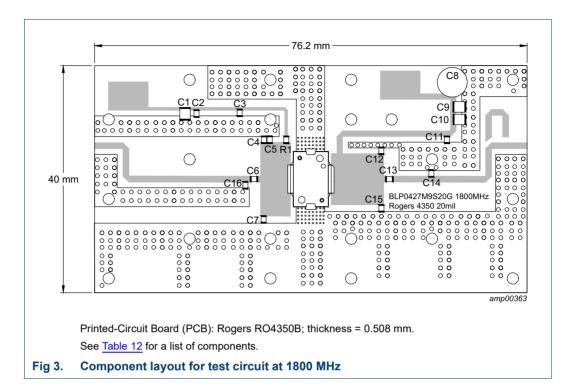


Table 12. List of components

See Figure 3 for component layout.

Component	Description	Value	Remarks
C1, C9, C10	multilayer ceramic chip capacitor	10 μF, 50 V	Murata
C2, C3, C11, C13	multilayer ceramic chip capacitor	12 pF	ATC 600F
C4, C5	multilayer ceramic chip capacitor	0.8 pF	ATC 600F
C6	multilayer ceramic chip capacitor	6.2 pF	ATC 600F
C7	multilayer ceramic chip capacitor	2 pF	ATC 600F
C8	electrolytic capacitor	2200 μF, 50 V	
C12, C15	multilayer ceramic chip capacitor	0.3 pF	ATC 600F
C14	multilayer ceramic chip capacitor	2.2 pF	ATC 600F
C16	multilayer ceramic chip capacitor	0.3 pF	ATC 600F
R1	resistor	5.1 Ω	SMD 0805

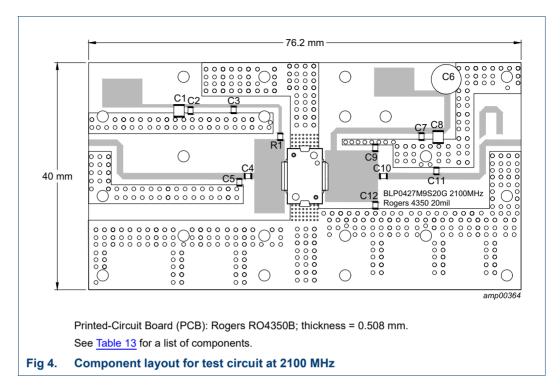


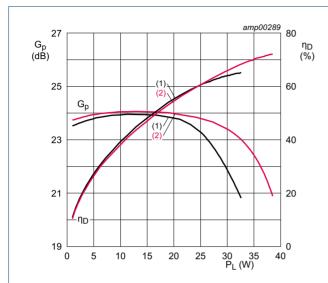
Table 13. List of components

See Figure 4 for component layout.

Component	Description	Value	Remarks
C1, C8	multilayer ceramic chip capacitor	10 μF, 50 V	Murata
C2, C7, C10	multilayer ceramic chip capacitor	12 pF	ATC 600F
C3	multilayer ceramic chip capacitor	62 pF	ATC 600F
C4	multilayer ceramic chip capacitor	5.6 pF	ATC 600F
C5	multilayer ceramic chip capacitor	0.5 pF	ATC 600F
C6	electrolytic capacitor	2200 μF, 50 V	
C9	multilayer ceramic chip capacitor	2.2 pF	ATC 600F
C11	multilayer ceramic chip capacitor	1.2 pF	ATC 600F
C12	multilayer ceramic chip capacitor	1.8 pF	ATC 600F
R1	resistor	5.1 Ω	SMD 0805

7.4 Graphical data

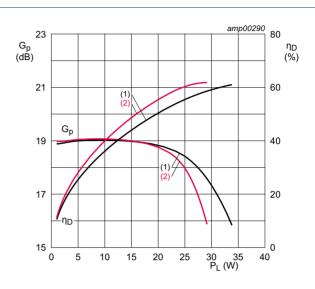
7.4.1 CW



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$

- (1) f = 728 MHz
- (2) f = 768 MHz

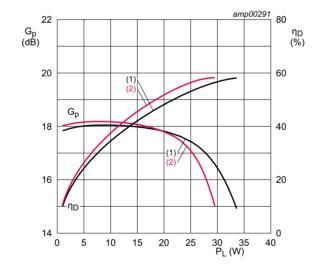
Fig 5. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 180 mA.

- (1) f = 1805 MHz
- (2) f = 1880 MHz

Fig 6. Power gain and drain efficiency as function of output power; typical values

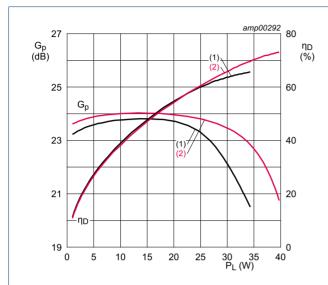


 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

Fig 7. Power gain and drain efficiency as function of output power; typical values

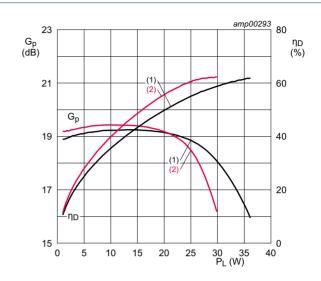
7.4.2 Pulsed CW



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$

- (1) f = 728 MHz
- (2) f = 768 MHz

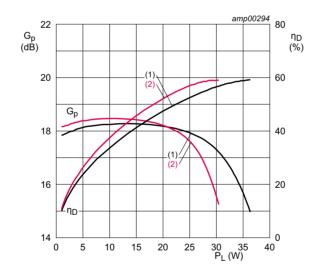
Fig 8. Power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$

- (1) f = 1805 MHz
- (2) f = 1880 MHz

Fig 9. Power gain and drain efficiency as function of output power; typical values

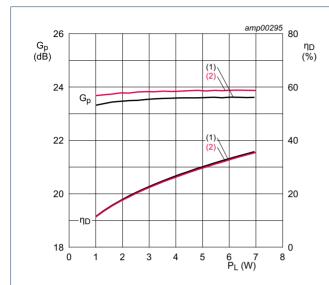


 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

Fig 10. Power gain and drain efficiency as function of output power; typical values

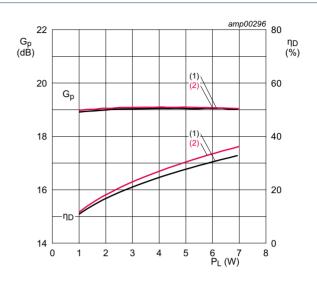
7.4.3 1-Carrier W-CDMA



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$

- (1) f = 728 MHz
- (2) f = 768 MHz

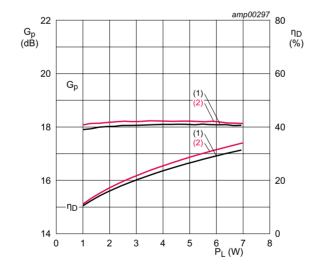
Fig 11. Power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$

- (1) f = 1805 MHz
- (2) f = 1880 MHz

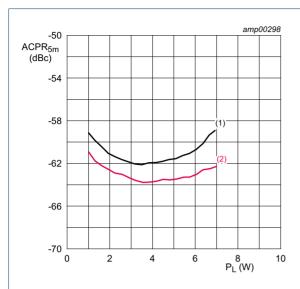
Fig 12. Power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

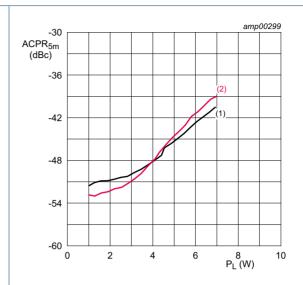
Fig 13. Power gain and drain efficiency as function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$

- (1) f = 728 MHz
- (2) f = 768 MHz

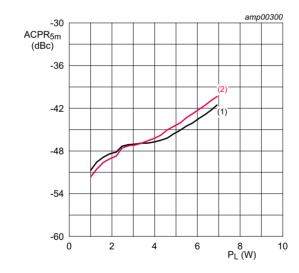
Fig 14. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$

- (1) f = 1805 MHz
- (2) f = 1880 MHz

Fig 15. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 180 \text{ mA}.$

- (1) f = 2110 MHz
- (2) f = 2170 MHz

Fig 16. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

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8. Package outline

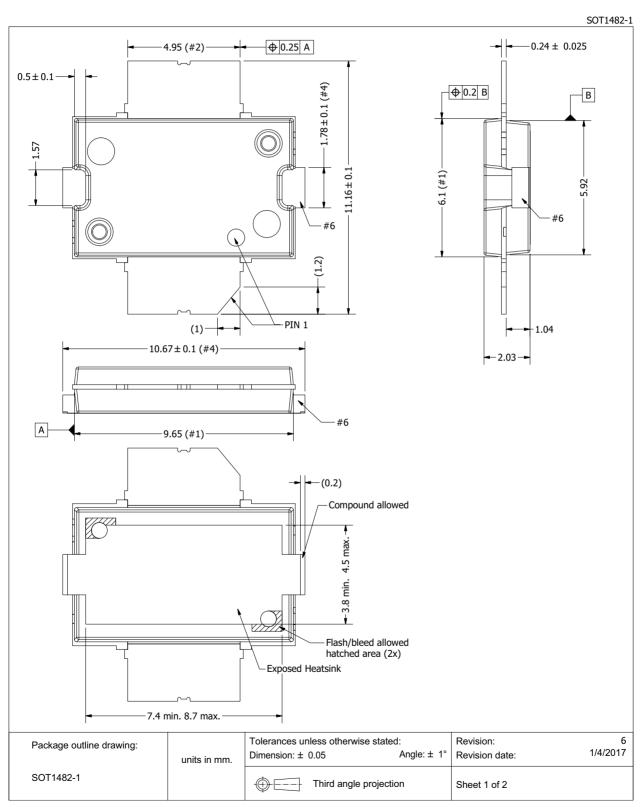
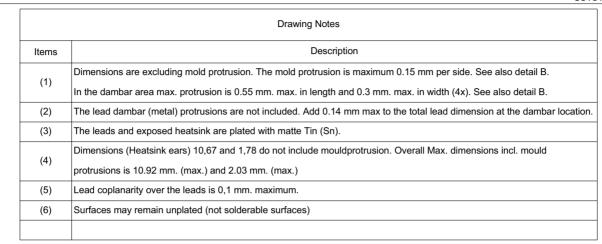


Fig 17. Package outline SOT1482-1 (sheet 1 of 2)

BLP0427M9S20_0427M9S20G

SOT1482-1



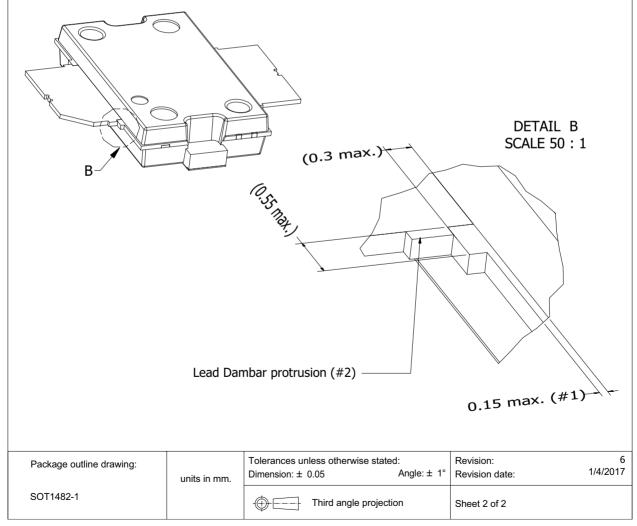


Fig 18. Package outline SOT1482-1 (sheet 2 of 2)

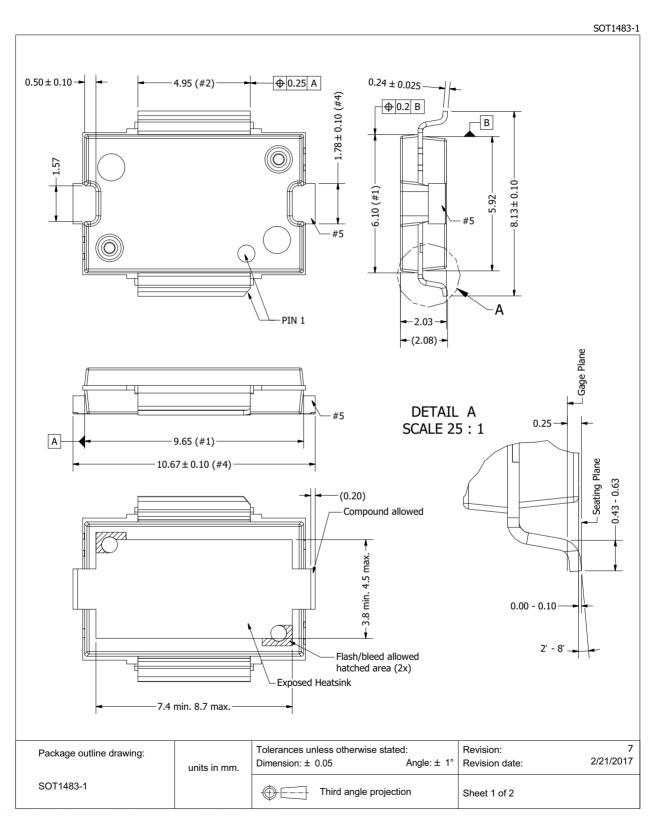
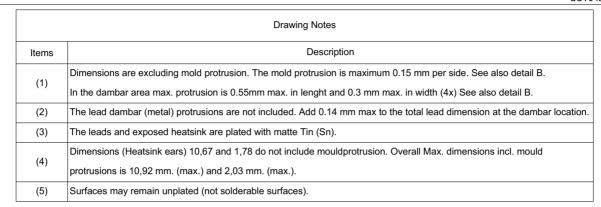


Fig 19. Package outline SOT1483-1 (sheet 1 of 2)

BLP0427M9S20_0427M9S20G

SOT1483-1



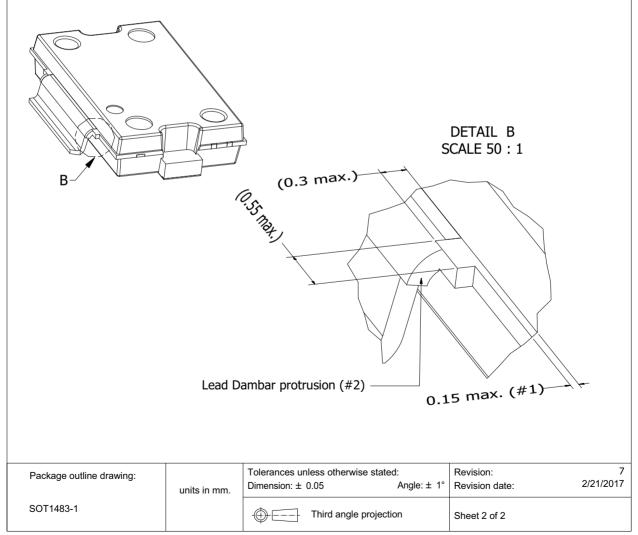


Fig 20. Package outline SOT1483-1 (sheet 2 of 2)

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 14. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

10. Abbreviations

Table 15. Abbreviations

Acronym	Description	
CW	Continuous Wave	
ESD	ElectroStatic Discharge	
LDMOS	Laterally Diffused Metal-Oxide Semiconductor	
SMD	Surface Mounted Device	
W-CDMA	Wideband Code Division Multiple Access	

11. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLP0427M9S20_0427M9S20G v.1	20180116	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL https://www.ampleon.com.

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